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thin solid films

Contents

Preface xiii

Publication schedule xiv

Committees xvi

Exhibitors xviii

OPTICAL THIN FILMS

Recent advances in optical coating materials

Quasicrystal films: numerical optimization as a solar selective absorber 1
T. Eisenhammer (Munich, Germany)

Patterning of multilayer dielectric optical coatings for multispectral CCDs 6
J.D. Barrie, K.A. Aitchison, G.S. Rossano (Los Angeles, CA, USA), M.H. Abraham (El Segundo, CA, USA)

Mid-infrared ($2.5 \leq \lambda \leq 12.5$ μm) optical absorption enhancement of textured silicon surfaces coated with an antireflective thin film 10
E.S. Kolesar, Jr. (Fort Worth, TX, USA), V.M. Bright, D.M. Sowders (Dayton, OH, USA)

Epitaxial growth of gallium nitride by ion-beam-assisted evaporation 16
C.-W. Jeon, S.-H. Kim, I.-H. Kim (Kyungbuk, South Korea)

New transparent conducting $MgIn_2O_4$–$Zn_2In_2O_5$ thin films prepared by magnetron sputtering 22
T. Minami, S. Takata, T. Kakumu, H. Sonohara (Ishikawa, Japan)

Influence of processing variables on the structure and properties of ZnO films 27
G.J. Exarhos (Richland, WA, USA), S.K. Sharma (Honolulu, HI, USA)

Zinc oxide thin films by the spray pyrolysis method 33
M. Krunks, E. Mellikov (Tallinn, Estonia)

Physics of very thin ITO conducting films with high transparency prepared by DC magnetron sputtering 37
T. Minami, H. Sonohara, T. Kakumu, S. Takata (Ishikawa, Japan)

Vacuum deposited polymer/metal multilayer films for optical application 43
J. Affinito, P. Martin, M. Gross, C. Coronado, E. Greenwell (Richland, WA, USA)

Fundamental aspects of optical thin films

Highly homogeneous silica coatings for optical and protective applications deposited by PECVD at room temperature in a planar uniform distributed electron cyclotron resonance plasma reactor 49
J.C. Rostaing, F. Coeuret (Jouy-en-Josas, France), J. Pelletier, T. Lagarde (Meylan, France), R. Etemadi (Palaiseau, France)

Photon frequency dependent electron relaxation time in noble metals: effect of voids 55
T. Eisenhammer (Munich, Germany)

GaGeTe films as phase-change optical recording media 60
Y. Sripathi, L.K. Malhotra (New Delhi, India)

Ellipsometry: film measurement and growth control

In-situ ellipsometry on sputtered dielectric and magneto-optic thin films 65
S. Heckens, J.A. Woollam (Lincoln, NE, USA)

Preparation and characterization of oxidized silver thin films 69
L.A.A. Pettersson, P.G. Snyder (Lincoln, NE, USA)

Elsevier Science S.A.

In-situ ellipsometric characterization of the electrodeposition of metal films 73
J.N. Hilfiker, D.W. Thompson, J.S. Hale, J.A. Woollam (Lincoln, NE, USA)

Numerical techniques useful in the practice of ellipsometry 78
J.C. Comforta, F.K. Urban III (Miami, FL, USA)

Dielectric reference coatings for the evaluation of thin film characterization techniques 85
U. Beck, G. Reiners (Berlin, Germany)

Applications of variable angle spectroscopic ellipsometry to strained SiGe alloy heterostructures 91
A.R. Heyd, S.A. Alterovitz (Cleveland, OH, USA), E.T. Croke (Malibu, CA, USA), K.L. Wang, C.H. Lee (Los Angeles, CA, USA)

Optical thin films (poster session)

Characterization of $In_{0.48}Ga_{0.52}P$-based thin-layer structures using spectroscopic ellipsometry 97
K. Watanabe, K. Kobayashi, C.C. Wong, Y.-M. Xiong, T. Saitoh (Tokyo, Japan), F. Hyuga (Kanagawa, Japan)

Microstructure and optical properties of plasmapolymer thin films with embedded silver nanoparticles 103
A. Heilmann, J. Werner, D. Schwarzenberg (Chemnitz, Germany), S. Henkel, P. Grosse, W. Thei (Aachen, Germany)

HMDSO plasma polymerization and thin film optical properties 109
R.P. Mota (Guaratinguetá, SP, Brazil), D. Galvão, S.F. Durrant, M.A. Bica de Moraes (Campinas, SP, Brazil), S.d.O. Dantas (Juiz de Fora, MG, Brazil), M. Cantão (Campinas, SP, Brazil)

Optical properties of non-stoichiometric SiO_2 as a function of excess silicon content and thermal treatments 114
W. Calleja (Puebla, Pue., Mexico), C. Falcony (Mexico D.F., Mexico), A. Torres, M. Aceves (Puebla, Pue., Mexico), R. Osorio (Mexico, D.F., Mexico)

DIAMOND AND RELATED MATERIALS

Synthesis, characterization and applications of cubic boron nitride and CN materials

Comparison of the properties of BN films synthesized by inductively coupled r.f. and microwave plasmas 118
F. Kiel, M. Cotarelo, M.P. Delplancke, R. Winand (Brussels, Belgium)

Synthesis and characterization of diamond and related materials

Investigation of the nucleation mechanism in bias-enhanced diamond deposition on silicon and molybdenum 124
P. Reinke, P. Kania, P. Oelhafen (Basel, Switzerland)

Pulsed ion beam characterization of CVD diamond surfaces under thin film deposition conditions 130
A.R. Krauss, J. Im (Argonne, IL, USA), J.A. Schultz (Houston, TX, USA), V.S. Smentkowski (Argonne, IL, USA), K. Waters (Houston, TX, USA), C.D. Zuiker, D.M. Gruen (Argonne, IL, USA), R.P.H. Chang (Evanston IL, USA)

Residual stress, Young's modulus and fracture stress of hot flame deposited diamond 137
P. Hollman, A. Alahelisten, M. Olsson, S. Hogmark (Uppsala, Sweden)

High-temperature Raman study in CVD diamond 143
K.-H. Chen, Y.-L. Lai, L.-C. Chen (Taipei, Taiwan), J.-Y. Wu, F.-J. Kao (Kaohsiung, Taiwan)

Effect of nitrogen on diamond growth using unconventional gas mixtures 148
T.-M. Hong, S.-H. Chen, Y.-S. Chiou, C.-F. Chen (Hsinchu, Taiwan)

Physical and tribological properties of diamond films grown in argon-carbon plasmas 154
C. Zuiker, A.R. Krauss, D.M. Gruen, X. Pan, J.C. Li, R. Csencsits, A. Erdemir, C. Bindal, G. Fenske (Argonne, IL, USA)

Photoluminescence in amorphous carbon thin films and its relation to the microscopic properties 160
. Rusli, G.A.J. Amaratunga, S.R.P. Silva (Cambridge, UK)

Characterization of ion-beam-deposited diamond-like carbon films 165
V. Palshin, E.I. Meletis (Baton Rouge, LA, USA), S. Ves, S. Logothetidis (Thessaloniki, Greece)

Precursor gas effect on the mechanical and optical properties of ion beam deposited diamond-like carbon films 173
J.U. Oh, K.-R. Lee, K.Y. Eun (Seoul, South Korea)

Characterization of diamond films deposited on titanium and its alloys 177
D. Rats, L. Vandenbulcke, R. Herbin, R. Benoit, R. Erre (Orléans, France), V. Serin, J. Sevely (Toulouse, France)

Adhesion of diamond coatings on cemented carbides 184
M. Nesládek, K. Vandierendonck, C. Quaeyhaegens, M. Kerkhofs, L.M. Stals (Diepenbeek, Belgium)

Electronic and optical applications of diamond and related materials

Electrical characterization of CVD diamond thin films grown on silicon substrates 189
A.K. Kulkarni, K. Tey, H. Rodrigo (Houghton, MI, USA)

Doping of rf plasma deposited diamond-like carbon films 194
S.R.P. Silva, G.A.J. Amaratunga (Cambridge, UK)

Photoelectron spectroscopy of ion-irradiated B-doped CVD diamond surfaces 200
G. Francz, P. Reinke, P. Oelhafen (Basel, Switzerland), W. Hänni (Neuchâtel, Switzerland)

Electrical properties of diamond films grown at low temperature 205
C.-F. Chen, S.-H. Chen, K.-M. Lin (Hsinchu, Taiwan, ROC)

Growth and morphological studies of (100) textured diamond thin films by microwave plasma-enhanced chemical vapor deposition 210
B.X. Yang, Y. Zhu, J. Ahn, H.S. Tan, D. Lu (Singapore, Singapore)

Diamond and related materials (poster session)

Optical study of ion-deposited diamond-like carbon films using spectroscopic ellipsometry 215
T. Mori, N. Fujii, Y.-M. Xiong, T. Saitoh (Tokyo, Japan)

Stress reduction for hard amorphous hydrogenated carbon thin films deposited by the self-bias method 220
H. Yamada (Tochigi, Japan), O. Tsuji (Kyoto, Japan), P. Wood (Sunnyvale, CA, USA)

TRIBOLOGICAL COATINGS/SURFACE MODIFICATIONS

Mechanical processes on the atomic scale

Non-linear optical spectroscopy of interfaces: adsorption sites of a self-assembled alkyl thiol monolayer/Au(111) 226
M.S. Yeganeh, S.M. Dougal, R.S. Polizzotti, P. Rabinowitz (Annandale, NJ, USA)

ADVANCES IN COATING AND THIN FILM CHARACTERIZATION

Mechanical properties and film adhesion

Characterization and adhesion study of thin alumina coatings sputtered on PET 230
R. Cueff, G. Baud (Aubière, France), M. Benmalek (Voreppe, France), J.P. Besse (Aubière, France), J. R Butruille, H.M. Dunlop (Voreppe, France), M. Jacquet (Aubière, France)

Effect of ion irradiation on internal stress of amorphic carbon films produced by pulsed laser 237
W.M. Kim, S.K. Lee, B. Cheong, S.G. Kim, O.S. Kim, J.S. Ro (Seoul, South Korea)

Creep studies of the EB PVD coatings with a ceramic layer 243
A.A. Tchizhik, L.B. Getsov, A.I. Rybnikov (St. Petersburg, Russia), I.S. Malashenko (Kiev, Ukraine)

Thermal cyclic response of EB PVD yttria-stabilized zirconia/CoCrAlY coatings 247
A.I. Rybnikov, L.B. Getsov (St. Petersburg, Russia), I.S. Malashenko (Kiev, Ukraine)

Properties of thin TiN films deposited onto stainless steel by an in-line dry coating process 253
Y. Miyamoto, Y. Kubo (Kawasaki, Japan), N. Ono (Yamaguchi Pre., Japan), M. Hashimoto (Kawasaki, Japan), T. Takahashi (Yamaguchi Pre., Japan), I. Ito (Tokyo, Japan), F. Arezzo, P. Gimondo (Roma, Italy)

Effect of Ar gas pressure on growth, structure, and mechanical properties of sputtered Ti, Al, TiAl, and Ti_3Al films 260
M. Chinmulgund, R.B. Inturi, J.A. Barnard (Tuscaloosa, AL, USA)

Mechanical measurement of the residual stress in thin PVD films 264
R.O.E. Vijgen, J.H. Dautzenberg (Eindhoven, The Netherlands)

A method for elastic modulus measurements of magnetron sputtered thin films dedicated to mechanical applications 270
A. Rouzaud, E. Barbier, J. Ernoult, E. Quesnel (Grenoble, France)

Deposition of diamond-like carbon on a titanium biomedical alloy 275
N.J. Ianno, R.O. Dillon, A. Ali, A. Ahmad (Lincoln, NE, USA)

Comparison between analytical and FEM calculations for the contact problem of spherical indenters on layered materials 279
N. Schwarzer (Chemnitz, Germany), H. Djabella (Manchester, UK), F. Richter (Chemnitz, Germany), R.D. Arnell (Manchester, UK)

Influence of thickness and substrate on the hardness and deformation of TiN films 283
M. Wittling, A. Bendavid, P.J. Martin, M.V. Swain (Lindfield, NSW, Australia)

Nondestructive and in situ characterization

Characterization of native, and adsorbed thin films on silicon detector surfaces: static and kinetic applications 289
R.M.A. Azzam (New Orleans, LA, USA)

Holographic characterization of azo-dye doped poly(methyl methacrylate) films 295
V.P. Pham, G. Manivannan, R.A. Lessard (Cité universitaire, Qué., Canada)

Photoellipsometry studies of δ-doped GaAs and modulation-doped AlGaAs/GaAs heterojunction structures 300
Y.-M. Xiong, C.C. Wong, T. Saitoh (Tokyo, Japan)

Structural characterization of ion-beam-induced epitaxially crystallized thin layers of III–V and IV–IV semiconductors 307
N. Kobayashi (Ibaraki, Japan)

UHV RHEED system for in-situ studies of sputtered films 314
S.R. Das, L. LeBrun (Ottawa, Ont., Canada), P.B. Sewell (Woodlawn, Ont., Canada), T. Tyrie (Wilton, NH, USA)

Effect of process parameter changes on the composition of magnetron sputtered and evaporated TiN and AlN films measured by UHV in-situ techniques 320
R. Roth, J. Schubert, M. Martin, E. Fromm (Stuttgart, Germany)

Surface and thin film analysis

Influence of the plasma pretreatment of a steel substrate on the development of an hydrogenated carbon deposit 325
P.V. Brande, S. Lucas, A. Weymeersch, L. Renard (Liège, Belgium), J.-M. Vanseveren, R. Winand (Bruxelles, Belgium)

Comparative analysis of razor blade coatings using Auger electron spectroscopy 331
R.L. Moore (Plainsboro, NJ, USA)

Characterization of the surface of bio-ceramic thin films 335
A.M. Ektessabi, H. Kimura (Sakyoku, Kyoto, Japan)

Characterization of intermetallic phases and oxides formed in annealed Ni/Al multilayer structures 341
A. Zalar (Ljubljana, Slovenia), S. Hofmann, D. Kohl (Stuttgart, Germany), P. Panjan (Ljubljana, Slovenia)

Microstructural characterization and imaging techniques

Segregation of Cu in Cu(Ti) alloys during nitridation in NH_3 346
D. Adams, T.L. Alford, N.D. Theodore, S.W. Russell (Tempe, AZ, USA)

Electron beam initiated oxidation and coalescence of metal particles embedded in a plasma–polymer thin film matrix 351
A. Heilmann, A.D. Müller, J. Werner, F. Müller (Chemnitz, Germany)

Artifacts in SPM measurements of thin films and coatings 356
T.G. Lenihan, A.P. Malshe, W.D. Brown, L.W. Schaper (Fayetteville, AR, USA)

Advances in coating and thin film characterization (poster session)

Fracture mechanisms of ceramic coating during wear 362
D.F. Diao, Y. Sawaki (Hamamatsu, Japan)

A continuous electrical resistivity measurement in thin films 367
A. Cvelbar, P. Panjan, B. Navinšek, A. Zalar, M. Budnar, L. Trontelj (Ljubljana, Slovenia)

The analytical solution of the contact problem of spherical indenters on layered materials: application for the investigation of TiN films on silicon 371
N. Schwarzer (Chemnitz, Germany), M. Whittling, M. Swain (Lindfield, NSW, Australia), F. Richter (Chemnitz, Germany)

D.c. properties of ZnO thin films prepared by r.f. magnetron sputtering 376
F.S. Mahmood, R.D. Gould, A.K. Hassan, H.M. Salih (Keele, UK)

The changes of structure upon thermal treatment of gold coatings electrodeposited on vacuum-sputtered Ti and electrodeposited Ni–B or Ni–Fe layers 380
I. Vītiņa, M. Lubāne, A. Korne, V. Rubene, V. Belmane, Z. Zariņa, A. Krūmiņa (Salaspils, LV, Latvia)

Space-charge-limited conductivity in evaporated cadmium selenide thin films 387
A.O. Oduor, R.D. Gould (Keele, UK)

Micromechanical properties of amorphous carbon coatings deposited by different deposition techniques 391
B.K. Gupta, B. Bhushan (Columbus, OH, USA)

Surface analysis algorithms for scanning probe microscopy 399
C.S. Lindquist, F.K. Urban III (Miami, FL, USA)

Structural and optical characterization of β-$FeSi_2$ layers on Si formed by ion beam synthesis 406
N. Kobayashi, H. Katsumata, H.L. Shen, M. Hasegawa, Y. Makita, H. Shibata, S. Kimura, A. Obara (Ibaraki, Japan), S. Uekusa (Kanagawa, Japan), T. Hatano (Tsukuba, Japan)

Mechanical properties and adhesion strength of TiN and Al coatings on HSS, steel, aluminium and copper characterized by four testing Methods 411
D. Müller, E. Fromm (Stuttgart, Germany)

Surface modification of aluminum alloys in molten salts containing $CeCl_3$ 417
F. Mansfeld (Los Angeles, CA, USA), F.J. Pérez (Madrid, Spain)

Ion-beam-induced insulator deposition for chip circuit modification 422
L. Hahn, M. Abramo, L. Moszkowicz (Essex Junction, VT, USA), A. Doyle, D. Stewart (Peabody, MA, USA)

Roughness determination of plasma-modified surface layers with atomic force microscopy 426
N. Almqvist (Luleå, Sweden), M. Rubel (Stockholm, Sweden), P. Wienhold (Jülich, Germany), S. Fredriksson (Luleå, Sweden)

Evaluation of PVD nitride coatings, using impact, scratch and Rockwell-C adhesion tests 431
W. Heinke, A. Leyland, A. Matthews (Hull, UK), G. Berg, C. Friedrich, E. Broszeit (Darmstadt, Germany)

ADVANCED MATERIALS IN MICROELECTRONICS

Advanced metallization: materials and processes

Improving electromigration reliability in Al–alloy lines 439
G. Rajagopalan (Tempe, AZ, USA), M.L. Dreyer, N.D. Theodore (Mesa, AZ, USA), T.S. Cale (Tempe, AZ, USA)

Growth mechanism of Si nodules on BPSG 445
C. Noritake, I. Kondo, K. Kondo, O. Takenaka (Aichi, Japan), A. Kinbara (Ishikawa, Japan)

A study of hillock formation on Al–Ta alloy films for interconnections of TFT–LCDs 450
E. Iwamura, T. Ohnishi, K. Yoshikawa (Kobe, Japan)

A detailed model for low-pressure CVD of tungsten 456
K.J. Kuijlaars, C.R. Kleijn, H.E.A. van den Akker (Delft, The Netherlands)

Selective tungsten CVD on submicron contact hole 462
W.-K. Yeh, M.-C. Chen, P.-J. Wang, L.-M. Liu, M.-S. Lin (Hsinchu, Taiwan)

Non-destructive determination of step coverage on semiconductor wafers 467
W.H. Johnson (Santa Clara, CA, USA), B. Brennan (Austin, TX, USA)

Integration of copper multilevel interconnects with oxide and polymer interlevel dielectrics 472
R.J. Gutmann, T. Paul Chow, S. Lakshminarayanan, D.T. Price, J.M. Steigerwald, L. You, S.P. Murarka (Troy, NY, USA)

The chemical vapor deposition of copper and copper alloys 480
P. Doppelt, T.H. Baum (San Jose, CA, USA)

Growth, selectivity and adhesion of CVD-deposited copper from Cu^{+1} (hexafluoroacetylacetonate trimethylvinylsilane) and dichlorodimethylsilane 483
J.B. Webb, D. Northcott (Ottawa, Ont., Canada), I. Emesh (Nepean, Ont., Canada)

A novel technique for fabrication of metallic structures on polyimide by selective electroless copper plating using ion implantation 489
S. Bhansali, D.K. Sood (Melbourne, Australia)

Normal metal, ohmic contacts to high-temperature superconducting $YBa_2Cu_3O_{7-\delta}$ thin films suitable for multichip modules 493
D.A. Conte, W.D. Brown, S.S. Ang, H.A. Naseem (Fayetteville, AR, USA)

Advanced dielectrics and planarization: materials and processes

Study of the material properties and suitability of plasma-deposited fluorine-doped silicon dioxides for low dielectric constant interlevel dielectrics 498
V.L. Shannon, M.Z. Karim (Camas, WA, USA)

CVD of fluorosilicate glass for ULSI applications 503
M.J. Shapiro, S.V. Nguyen, T. Matsuda, D. Dobuzinsky (Hopewell Junction, NY, USA)

Crystallinity properties of parylene-n affecting its use as an ILD in submicron integrated circuit technology 508
X. Zhang (Troy, NY, USA), S. Dabral, C. Chiang (Santa Clara, CA, USA), J.F. McDonald, B. Wang (Troy, NY, USA)

Chemical and electrical characteristics of low temperature plasma enhanced CVD silicon oxide films using Si_2H_6 and N_2O 512
J. Song, G.S. Lee, P.K. Ajmera (Baton Rouge, LA, USA)

Low-temperature ($\leq$600 °C) semi-insulating oxygen-doped silicon films by the PECVD technique for large-area power applications 517
F.J. Clough, A.O. Brown (Cambridge, UK), S.N. Ekkanath Madathil (Leicester, UK), W.I. Milne (Cambridge, UK)

Diffusion barriers

Collimated Ti/TiN contact and barrier layers for sub 0.5 μm CVD W-filled contact holes 522
M. Biberger, S. Jackson, G. Tkach (Palo Alto, CA, USA), J. Schlueter, B. Jones, C.K. Huang (Austin, TX, USA), L. Ouellet (Bromont, Que., Canada)

Thermal stability of AlSiCu/W/n^+p diodes with and without TiN barrier layer 526
W.-K. Yeh, M.-C. Chen, P.-J. Wang, L.-M. Liu, M.-S. Lin (Hsinchu, Taiwan)

Metal–organic chemical vapor deposition of tantalum nitride barrier layers for ULSI applications 531
M.H. Tsai, S.C. Sun, C.P. Lee, H.T. Chiu, C.E. Tsai, S.H. Chaung, C.C. Wu (Hsinchu, Taiwan)

Silicides

0.10 μm $TiSi_2$ technology utilizing nitrogen diffusion controlled RTA 537
Y. Matsubara, T. Sakai, T. Ishigami, K. Ando, T. Horiuchi (Sagamihara, Japan)

Morphology and stability of $(Ti_{0.9}Zr_{0.1})Si_2$ thin films on Si(111) and Si(100) formed in UHV 544
Y. Dao, D.E. Sayers, R.J. Nemanich (Raleigh, NC, USA)

$CoSi_2$ and $TiSi_2$ for Si/SiGe heterodevices 549
M. Glück, A. Schüppen, M. Rösler, W. Heinrich, J. Hersener, U. König (Ulm, Germany), O. Yam, C. Cytermann, M. Eizenberg (Haifa, Israel)

Silicide formation and stability of Ti/SiGe and Co/SiGe 555
Z. Wang, D.B. Aldrich, Y.L. Chen, D.E. Sayers, R.J. Nemanich (Raleigh, NC, USA)

Initial stages in the formation of PtSi on Si(111) as followed by photoemission and spectroscopic ellipsometry 561
L. Ley (Erlangen, Germany), Y. Wang, V. Nguyen Van, S. Fisson, D. Souche, G. Vuye, J. Rivory (Paris, France)

Compatibility of NiSi in the self-aligned silicide process for deep submicrometer devices 567
R. Mukai, S. Ozawa, H. Yagi (Kawasaki, Japan)

Characterization of buried cobalt silicide layers in Si by MEVVA implantation 573
Q. Peng, S.P. Wong, I.H. Wilson, N. Wang, K.K. Fung (Hong Kong, Hong Kong)

Low power

SOI material qualification for low-power CMOS application 578
M.A. Mendicino, P.K. Vasudev, P. Maillot, C. Hoener, J. Baylis, J. Bennett, T. Boden, S. Jackett, K. Huffman, M. Godwin (Austin, TX, USA)

Ferroelectric non-volatile memories for low-voltage, low-power applications 584
R.E. Jones, Jr., P.D. Maniar (Austin, TX, USA), R. Moazzami (Boston, MA, USA), P. Zurcher, J.Z. Witowski, Y.T. Lii, P. Chu, S.J. Gillespie (Austin, TX, USA)

A thickness model for the $TiSi_2$/TiN stack in the titanium salicide process module 589
J.-Y. Tsai, P. Apte (Dallas, TX, USA)

Chemical–mechanical polishing

Chemical–mechanical polishing of copper with oxide and polymer interlevel dielectrics 596
R.J. Gutmann, J.M. Steigerwald, L. You, D.T. Price, J. Neirynck, D.J. Duquette, S.P. Murarka (Troy, NY, USA)

The effect of the polishing pad treatments on the chemical–mechanical polishing of SiO_2 films 601
W. Li, D.W. Shin, M. Tomozawa, S.P. Murarka (Troy, NY, USA)

Chemical mechanical polishing of PSG and BPSG dielectric films: the effect of phosphorus and boron concentration 607
C.-W. Liu, B.-T. Dai, C.-F. Yeh (Hsinchu, Taiwan)

Manufacturability of the CMP process 612
F. Malik, M. Hasan (Lahore, Pakistan)

Advanced materials in microelectronics (poster session)

Growth of dielectric layers on the InSb surface 616
A. Rastogi, K.V. Reddy (Madras, India)

Titanium nitride films for barrier applications produced by rapid thermal CVD and subsequent in-situ annealing. . . . 621
R. Leutenecker, B. Fröschle, U. Cao-Minh, P. Ramm (Munich, Germany)

Simulation of collimated flux distributions during physical vapor deposition 627
Z. Lin, T.S. Cale (Tempe, AZ, USA)

Heteroepitaxial $Si_{1-x-y}Ge_xC_y$ films on (100)Si substrates for future low-power applications 632
T.L. Alford, A.E. Bair, Z. Atzmon, L.M. Stout, S.G. Balster, D.K. Schroder, R.J. Roedel (Tempe, AZ, USA)

Recent developments in ionized cluster beam thin film deposition 637
A.J. Cox, J.J. Nainaparampil, M.F. Tabet, A. Hosseini-Tehrani, F.K. Urban III (Miami, FL, USA)

Author Index of Volume 270 643

Subject Index of Volume 270 645

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